BTA316-600BT

3Q Hi-Com Triac

Rev. 02 — 30 November 2010

Product data sheet

1. Product profile

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series BT" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber where "high junction operating temperature capability" is required

1.2 Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 600 | V |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5 | - | - | 140 | Α |
| Tj | junction temperature | | - | - | 150 | °C |
| I _{T(RMS)} | RMS on-state current | full sine wave; T _{mb} ≤ 126 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u> | - | - | 16 | Α |



Table 1. Quick reference data ...continued

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|----------------------|------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| Static cha | racteristics | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{C}}$ | 2 | - | 50 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$ | 2 | - | 50 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$ | 2 | - | 50 | mA |

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|--------------------------------|--------------------|----------------|
| 1 | T1 | main terminal 1 | | N . |
| 2 | T2 | main terminal 2 | mb | T2 — T1 |
| 3 | G | gate | | sym051 |
| mb | T2 | mounting base; main terminal 2 | 1 2 3 | |
| | | | SOT78 (TO-220AB) | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|--------------|----------|----------------------------------------------------------------------------------|---------|
| | Name | Description | Version |
| BTA316-600BT | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|-------------------------------------------------------------------------------------------------------------------|-----|-----|--------|
| V_{DRM} | repetitive peak off-state voltage | | - | 600 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_{mb} \le 126$ °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u> | - | 16 | Α |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u> | - | 140 | Α |
| | | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$ | - | 150 | Α |
| I ² t | I ² t for fusing | t _p = 10 ms; sine-wave pulse | - | 98 | A^2s |
| dI _T /dt | rate of rise of on-state current | $I_T = 20 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$ | - | 100 | A/µs |
| I _{GM} | peak gate current | | - | 2 | Α |
| P_{GM} | peak gate power | | - | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.5 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| T _j | junction temperature | | - | 150 | °C |

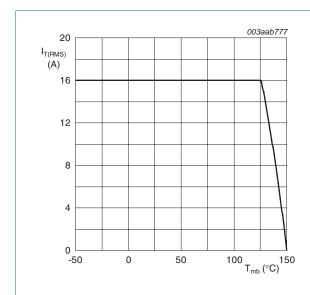
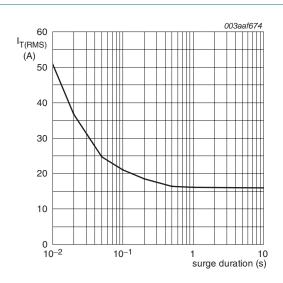


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{\text{mb}} = 126 \text{ }^{\circ}C$

Fig 2. RMS on-state current as a function of surge duration; maximum values

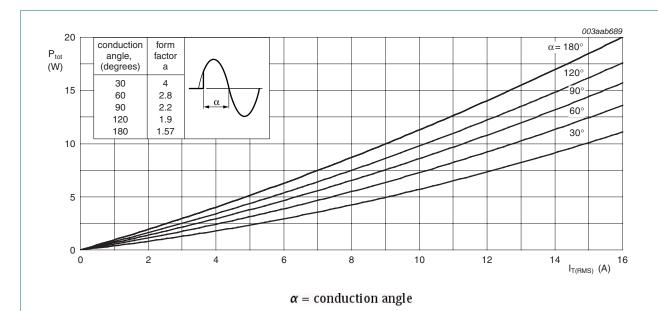


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

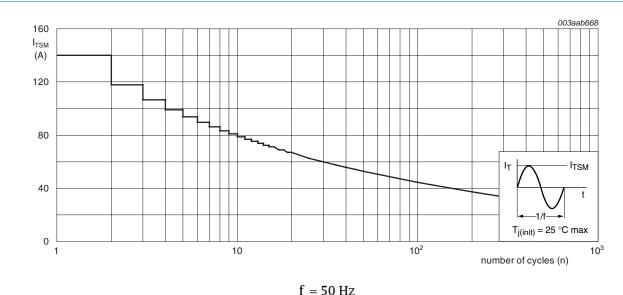
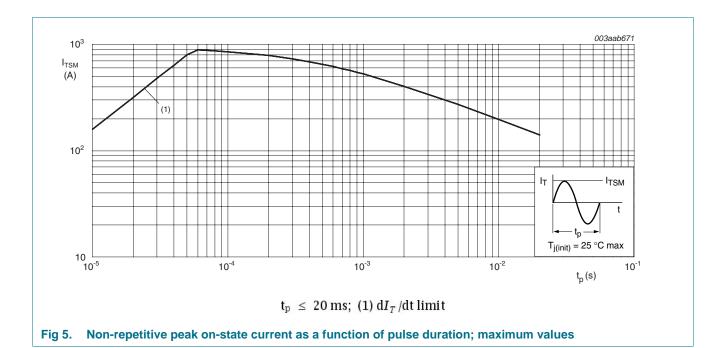


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------------|--------------------------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to | full cycle; see Figure 6 | - | - | 1.2 | K/W |
| | mounting base | half cycle; see Figure 6 | - | - | 1.7 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |

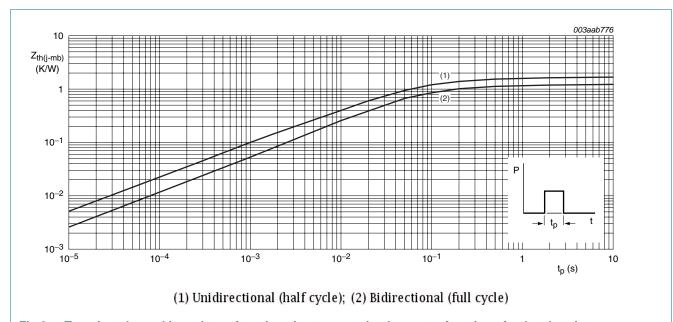


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

| Table 0. | Onaracteristics | | | | | |
|------------------------------------|-----------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------|------|------|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | racteristics | | | | | |
| I _{GT} gate trigger curre | gate trigger current | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+; T_j = 25 \text{ °C;}$ see Figure 7 | 2 | - | 50 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}\text{C};$ see Figure 7 | 2 | - | 50 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-}; T_j = 25 ^{\circ}\text{C};$ see Figure 7 | 2 | - | 50 | mA |
| I _L latching current | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+G+; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 8</u> | - | - | 60 | mA | |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8 | - | - | 90 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8 | - | - | 60 | mA |
| I _H | holding current | $V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } T_j}$ | - | - | 60 | mΑ |
| V_{T} | on-state voltage | $I_T = 18 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 10}{\text{Figure } 10}$ | - | 1.3 | 1.5 | V |
| V_{GT} | gate trigger voltage | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11 | - | 0.8 | 1.5 | V |
| | | $V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 \text{ °C};$ see Figure 11 | 0.25 | 0.4 | - | V |
| I _D | off-state current | $V_D = 600 \text{ V}; T_j = 150 ^{\circ}\text{C}$ | - | 0.24 | 1.2 | mΑ |
| Dynamic | characteristics | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 402 V; T_j = 150 °C; exponential waveform; gate open circuit | 600 | - | - | V/µs |
| dI _{com} /dt | rate of change of commutating current | V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 20 V/µs; "without snubber" condition; gate open circuit | 8 | - | - | A/ms |
| t _{gt} | gate-controlled turn-on time | $I_{TM} = 20 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$ | - | 2 | - | μs |

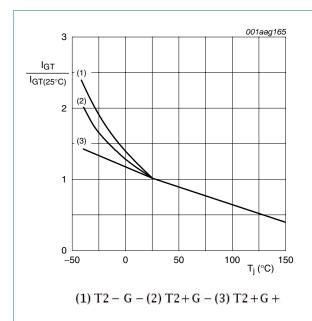


Fig 7. Normalized gate trigger current as a function of junction temperature

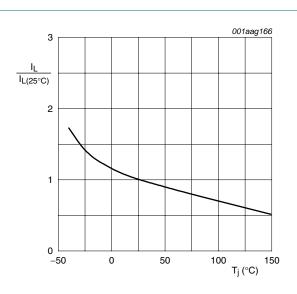


Fig 8. Normalized latching current as a function of junction temperature

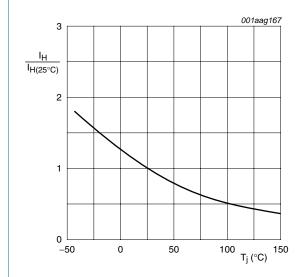
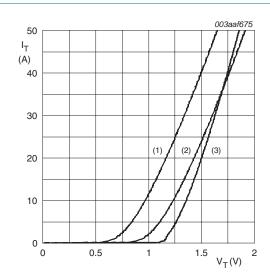


Fig 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.024 \text{ V}$

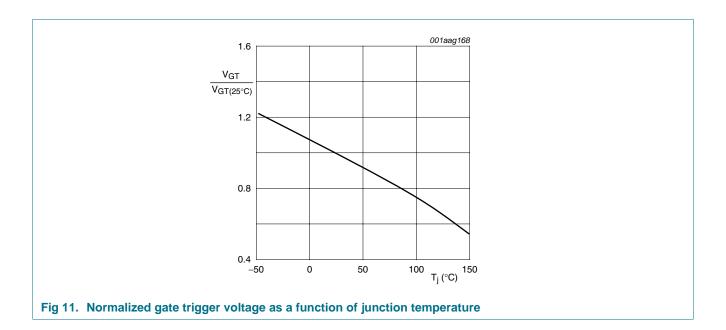
 $R_s = 0.021 \Omega$

(1) T_i = 150 °C; typical values

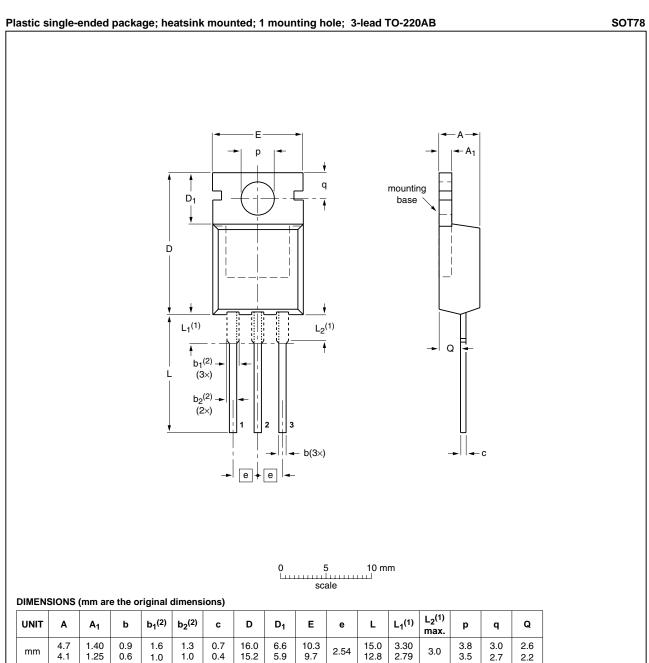
(2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage



Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE | | REFER | ENCES | EUROPEAN ISSUE D | |
|---------|-----|-----------------|-------|------------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | PROJECTION | ISSUE DATE |
| SOT78 | | 3-lead TO-220AB | SC-46 | | 08-04-23 08-06-13 |

Fig 12. Package outline SOT78 (TO-220AB)

BTA316-600BT

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8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------------|----------------------------------------|--------------------|---------------|-------------------|
| BTA316-600BT v.2 | 20101130 | Product data sheet | - | BTA316_SER_BT v.1 |
| Modifications: | Various changes to | content. | | |
| BTA316_SER_BT v.1 | 20070503 | Product data sheet | - | - |

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|--------------------------------|-------------------|---------------------------------------------------------------------------------------|
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